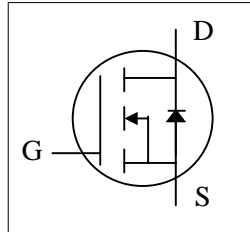




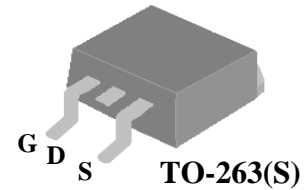
- ▼ Simple Drive Requirement
- ▼ Lower Gate Charge
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



| | |
|--------------|-------------|
| BV_{DSS} | 60V |
| $R_{DS(ON)}$ | 5m Ω |
| I_D | 80A |

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-263 package is widely preferred for commercial-industrial surface mount applications and suited for switching power applications.

Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|----------------------|--|------------|------------|
| V_{DS} | Drain-Source Voltage | 60 | V |
| V_{GS} | Gate-Source Voltage | +20 | V |
| $I_D@T_C=25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^3$ | 80 | A |
| I_{DM} | Pulsed Drain Current ¹ | 320 | A |
| $P_D@T_C=25^\circ C$ | Total Power Dissipation | 250 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Value | Units |
|--------|---|-------|--------------|
| Rthj-c | Maximum Thermal Resistance, Junction-case | 0.5 | $^\circ C/W$ |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient (PCB mount) ⁴ | 40 | $^\circ C/W$ |



AP98T06GS-HF

Electrical Characteristics @T_j=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------------|--|--|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 60 | - | - | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =40A | - | - | 5 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250uA | 2 | - | 4 | V |
| g _{fs} | Forward Transconductance | V _{DS} =10V, I _D =40A | - | 82 | - | S |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =48V, V _{GS} =0V | - | - | 25 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} = ±20V, V _{DS} =0V | - | - | ±100 | nA |
| Q _g | Total Gate Charge ² | I _D =40A | - | 92 | 150 | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =48V | - | 12 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =10V | - | 45 | - | nC |
| t _{d(on)} | Turn-on Delay Time ² | V _{DS} =30V | - | 17 | - | ns |
| t _r | Rise Time | I _D =40A | - | 75 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =3.3Ω, V _{GS} =10V | - | 45 | - | ns |
| t _f | Fall Time | R _D =0.75Ω | - | 85 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 3950 | 6300 | pF |
| C _{oss} | Output Capacitance | V _{DS} =25V | - | 1080 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 460 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|------------------------------------|--|------|------|------|-------|
| V _{SD} | Forward On Voltage ² | I _S =40A, V _{GS} =0V | - | - | 1.3 | V |
| t _{rr} | Reverse Recovery Time ² | I _S =40A, V _{GS} =0V | - | 70 | - | ns |
| Q _{rr} | Reverse Recovery Charge | di/dt=100A/μs | - | 160 | - | nC |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Package limitation current is 80A, calculated continuous current based on maximum allowable junction temperature is 171A.
- 4.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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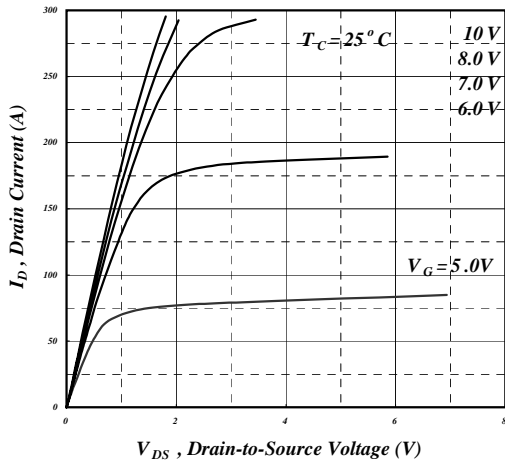


Fig 1. Typical Output Characteristics

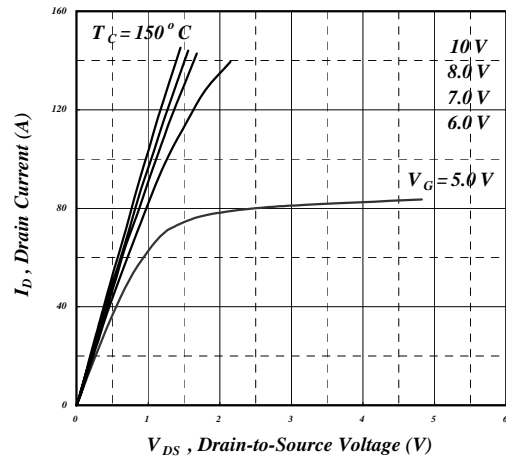


Fig 2. Typical Output Characteristics

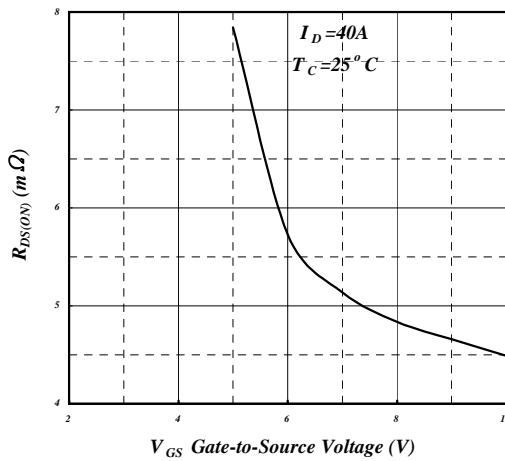


Fig 3. On-Resistance v.s. Gate Voltage

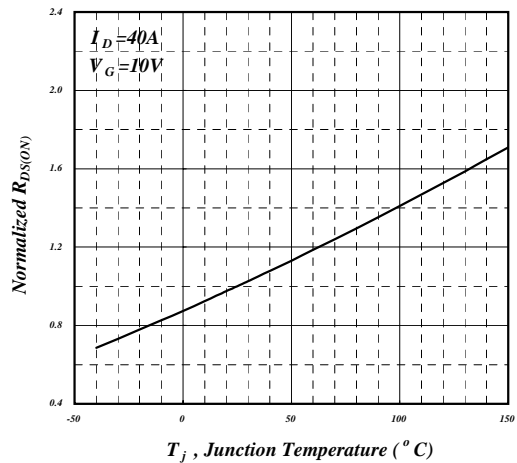


Fig 4. Normalized On-Resistance v.s. Junction Temperature

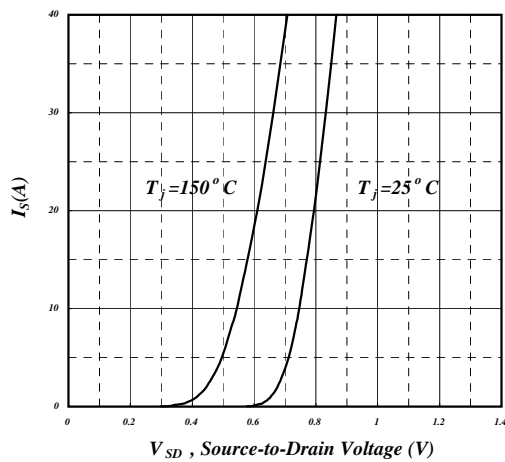


Fig 5. Forward Characteristic of Reverse Diode

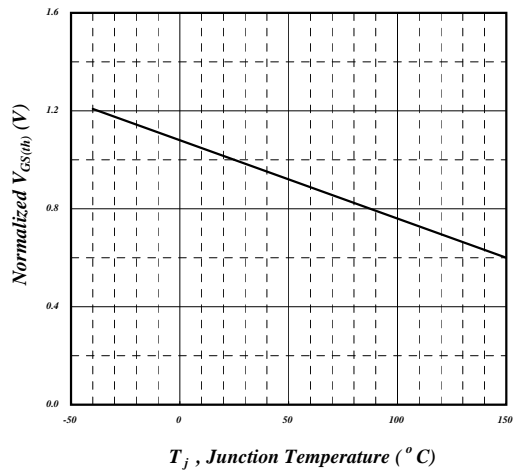


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



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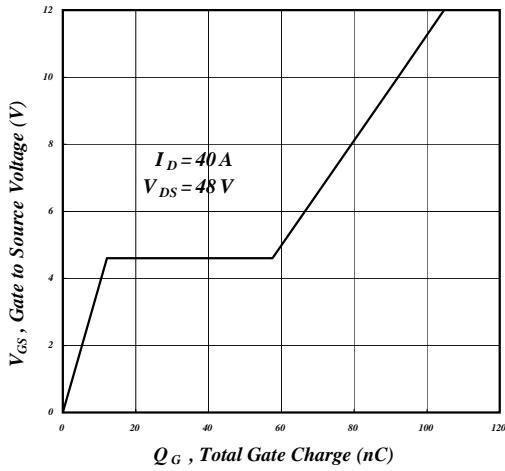


Fig 7. Gate Charge Characteristics

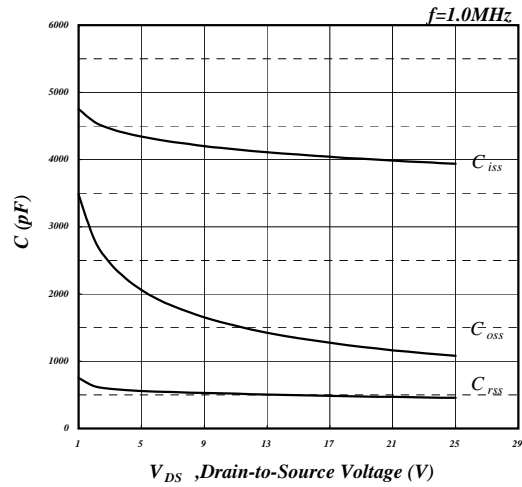


Fig 8. Typical Capacitance Characteristics

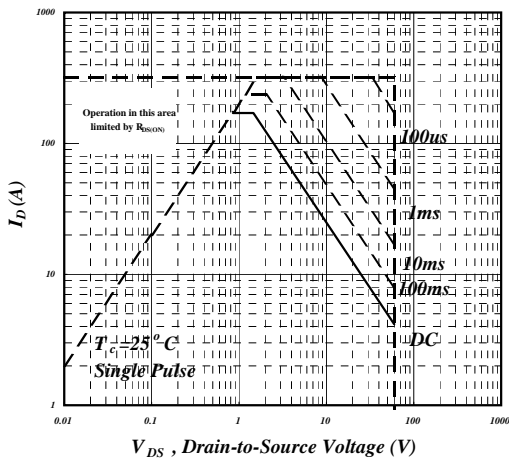


Fig 9. Maximum Safe Operating Area

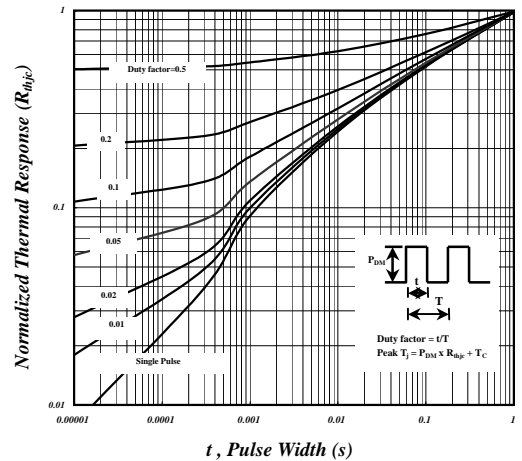


Fig 10. Effective Transient Thermal Impedance

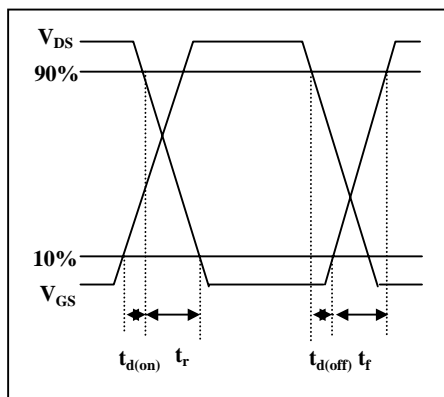


Fig 11. Switching Time Waveform

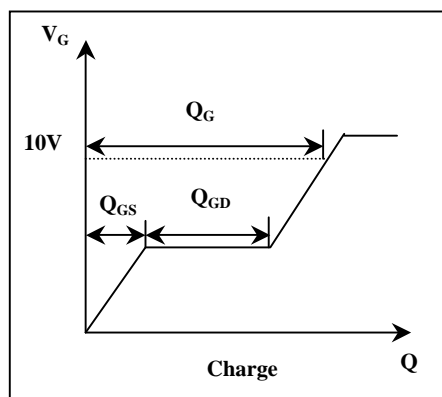


Fig 12. Gate Charge Waveform